

74AHC126; 74AHCT126

Quad buffer/line driver; 3-state

Rev. 04 — 12 August 2009

Product data sheet

1. General description

The 74AHC126; 74AHCT126 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC126; 74AHCT126 provides four non-inverting buffer/line drivers with 3-state outputs. The 3-state outputs (nY) are controlled by the output enable input (nOE). A LOW-level at pin nOE causes the outputs to assume a high-impedance OFF-state.

The 74AHC126; 74AHCT126 is identical to the 74AHC125; 74AHCT125 but has active HIGH output enable inputs.

2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger action
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ For 74AHC126: CMOS level
 - ◆ For 74AHCT126: TTL level
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AHC126D 74AHCT126D	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74AHC126PW 74AHCT126PW	−40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74AHC126BQ 74AHCT126BQ	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

4. Functional diagram

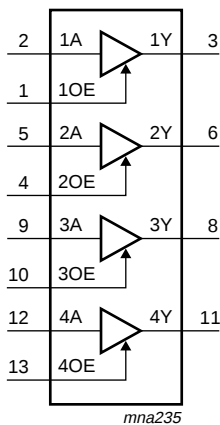


Fig 1. Functional diagram

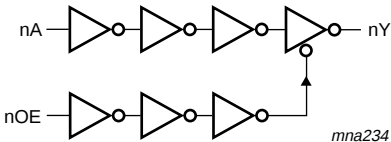


Fig 2. Logic symbol

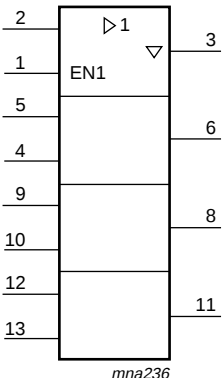
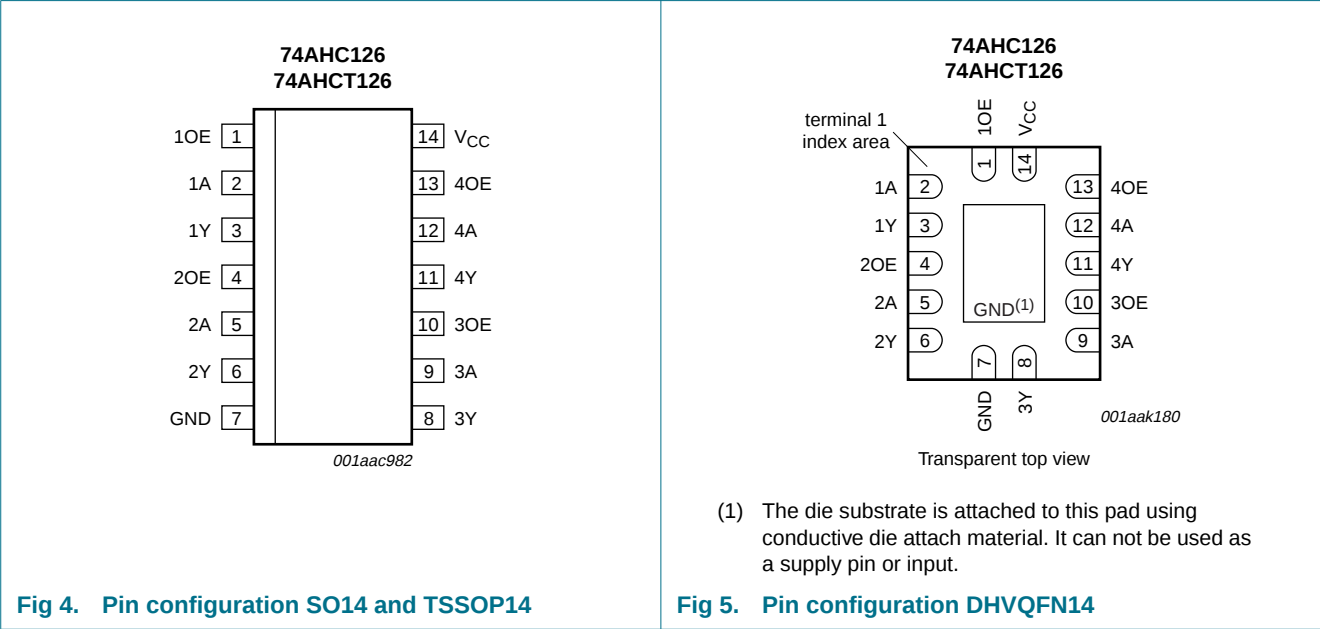


Fig 3. IEC logic symbol

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1OE	1	output enable input 1 (active HIGH)
1A	2	data input 1
1Y	3	data output 1
2OE	4	output enable input 2 (active HIGH)
2A	5	data input 2
2Y	6	data output 2
GND	7	ground (0 V)
3Y	8	data output 3
3A	9	data input 3
3OE	10	output enable input 3 (active HIGH)
4Y	11	data output 4
4A	12	data input 4
4OE	13	output enable input 4 (active HIGH)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Control	Input	Output
nOE	nA	nY
H	L	L
H	H	H
L	X	Z

- [1] H = HIGH voltage state;
 L = LOW voltage state;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
V _I	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	^[1] -20	-	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	^[1] -20	+20	mA
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	-25	+25	mA
I _{CC}	supply current		-	+75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[2] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] For SO14 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
 For TSSOP14 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.
 For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC126						
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	20	ns/V
74AHCT126						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC126										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = −50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = −8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_I	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	± 0.25	-	± 2.5	-	± 10.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μA
C_I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF
74AHCT126										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V}$ to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
		$I_O = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
		$I_O = 50 \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 5.5 \text{ V}$	-	-	± 0.25	-	± 2.5	-	± 10.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other pins at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	

74AHC126

t_{pd}	propagation delay	nA to nY; see Figure 6 ^[2]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$								
		$C_L = 15\text{ pF}$	-	4.7	8.0	1.0	9.5	1.0	10.0	ns
		$C_L = 50\text{ pF}$	-	6.7	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$								
		$C_L = 15\text{ pF}$	-	3.3	5.5	1.0	6.5	1.0	7.0	ns
t_{en}	enable time	nOE to nY; see Figure 7 ^[3]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$								
		$C_L = 15\text{ pF}$	-	5.3	8.0	1.0	9.5	1.0	10.0	ns
		$C_L = 50\text{ pF}$	-	7.6	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$								
		$C_L = 15\text{ pF}$	-	3.6	5.3	1.0	6.1	1.0	7.0	ns
t_{dis}	disable time	nOE to nY; see Figure 7 ^[4]								
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$								
		$C_L = 15\text{ pF}$	-	6.6	9.7	1.0	11.5	1.0	12.5	ns
		$C_L = 50\text{ pF}$	-	9.4	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$								
		$C_L = 15\text{ pF}$	-	4.7	6.8	1.0	8.0	1.0	8.5	ns
C_{PD}	power dissipation capacitance	$f_i = 1\text{ MHz}; V_i = \text{GND to }V_{CC}$ ^[5]	-	10	-	-	-	-	-	pF

74AHCT126; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$

t_{pd}	propagation delay	nA to nY; see Figure 6 ^[2]								
		$C_L = 15\text{ pF}$	-	3.0	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50\text{ pF}$	-	4.3	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	nOE to nY; see Figure 7 ^[3]								
		$C_L = 15\text{ pF}$	-	3.3	5.1	1.0	6.0	1.0	6.5	ns
		$C_L = 50\text{ pF}$	-	4.7	7.1	1.0	8.0	1.0	9.0	ns
t_{dis}	disable time	nOE to nY; see Figure 7 ^[4]								
		$C_L = 15\text{ pF}$	-	4.8	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50\text{ pF}$	-	6.9	8.9	1.0	10.0	1.0	11.5	ns
C_{PD}	power dissipation capacitance	$f_i = 1\text{ MHz}; V_i = \text{GND to }V_{CC}$ ^[5]	-	12	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3\text{ V}$ and $V_{CC} = 5.0\text{ V}$).

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] t_{en} is the same as t_{PZL} and t_{PZH} .

[4] t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

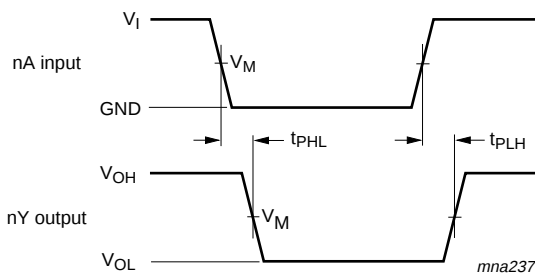
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

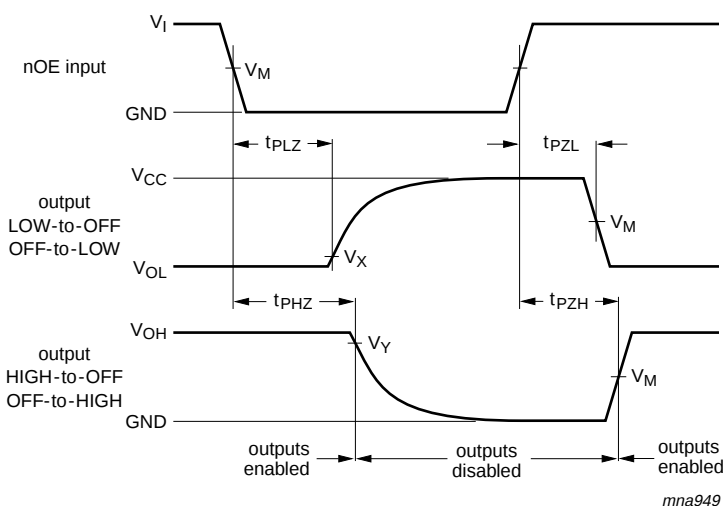
11. Waveforms



Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Input to output propagation delays



Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Enable and disable times

Table 8. Measurement points

Type	Input	Output		
	V _M	V _M	V _X	V _Y
74AHC126	0.5 × V _{CC}	0.5 × V _{CC}	V _{OL} + 0.3 V	V _{OH} − 0.3 V
74AHCT126	1.5 V	0.5 × V _{CC}	V _{OL} + 0.3 V	V _{OH} − 0.3 V

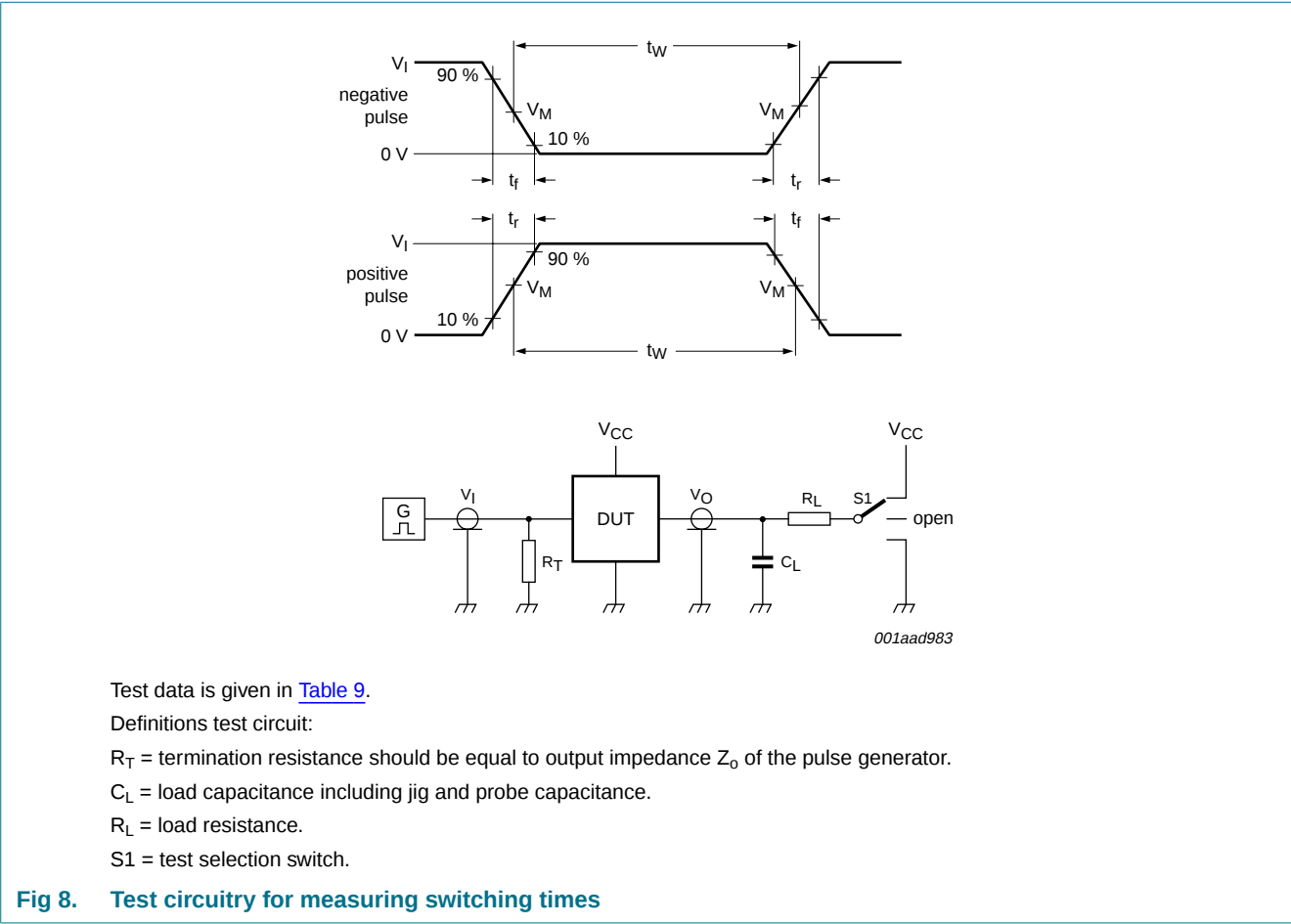


Fig 8. Test circuitry for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V _I	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74AHC126	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74AHCT126	3.0 V	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm SOT108-1

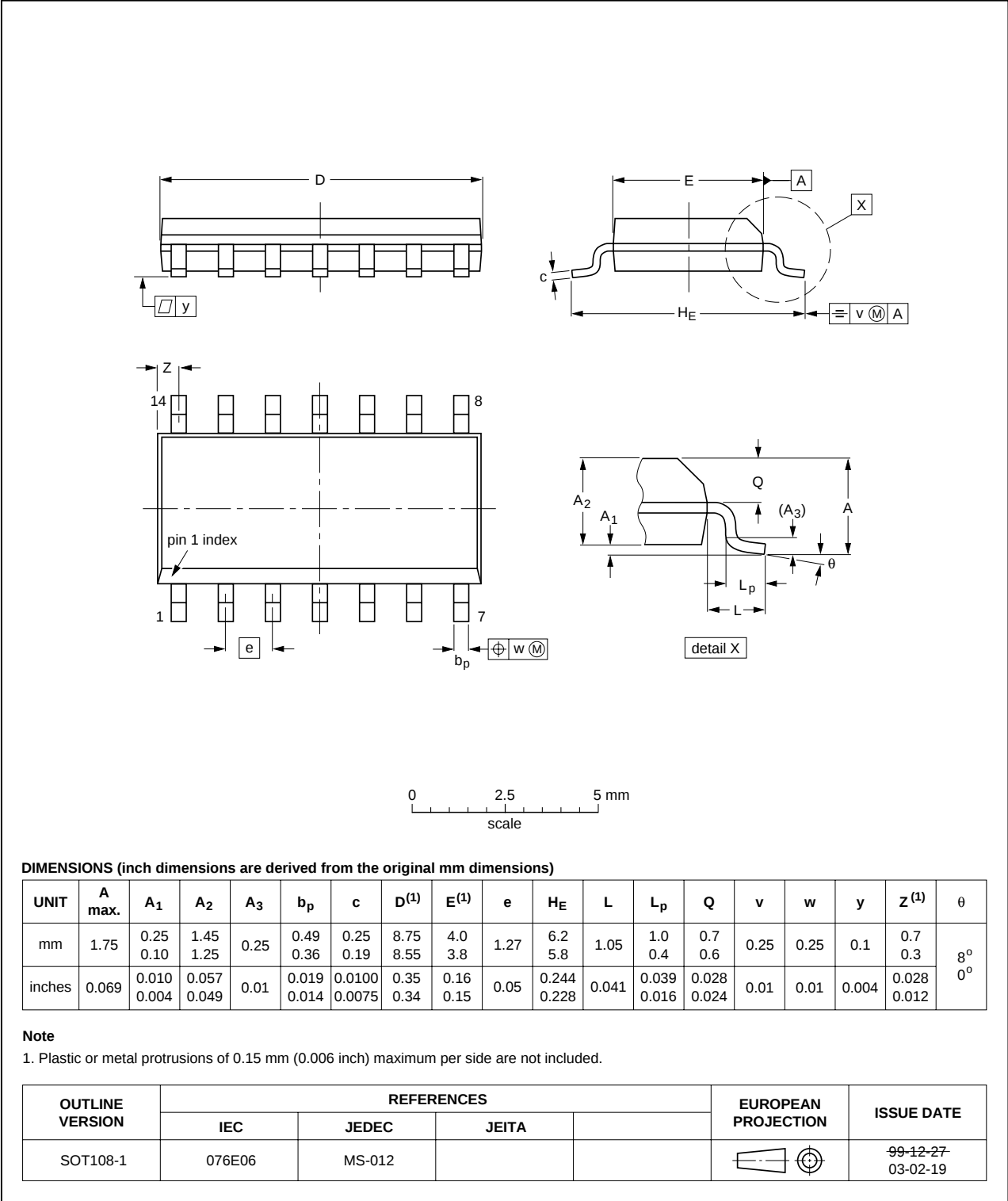


Fig 9. Package outline SOT108-1 (SO14)

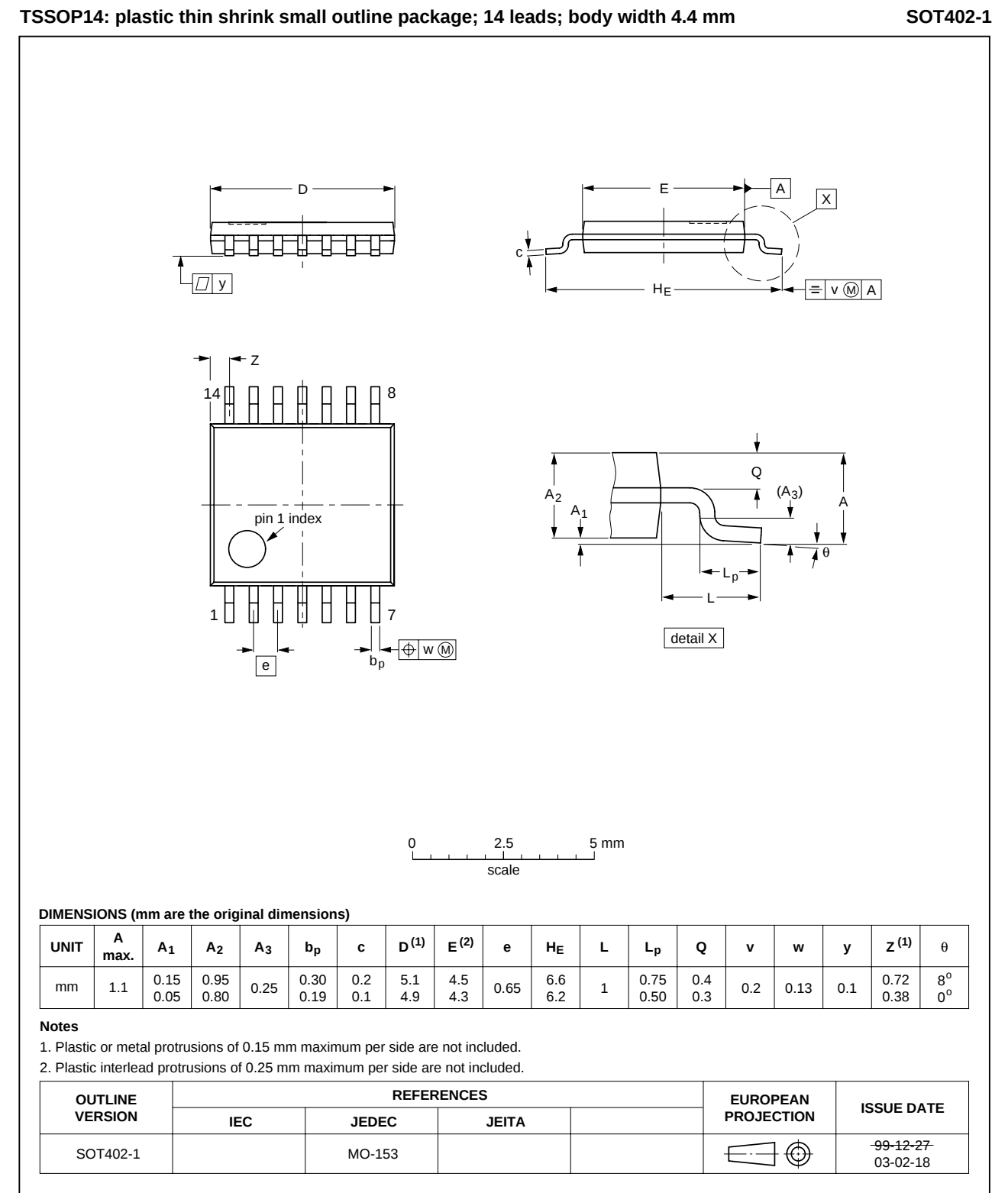


Fig 10. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

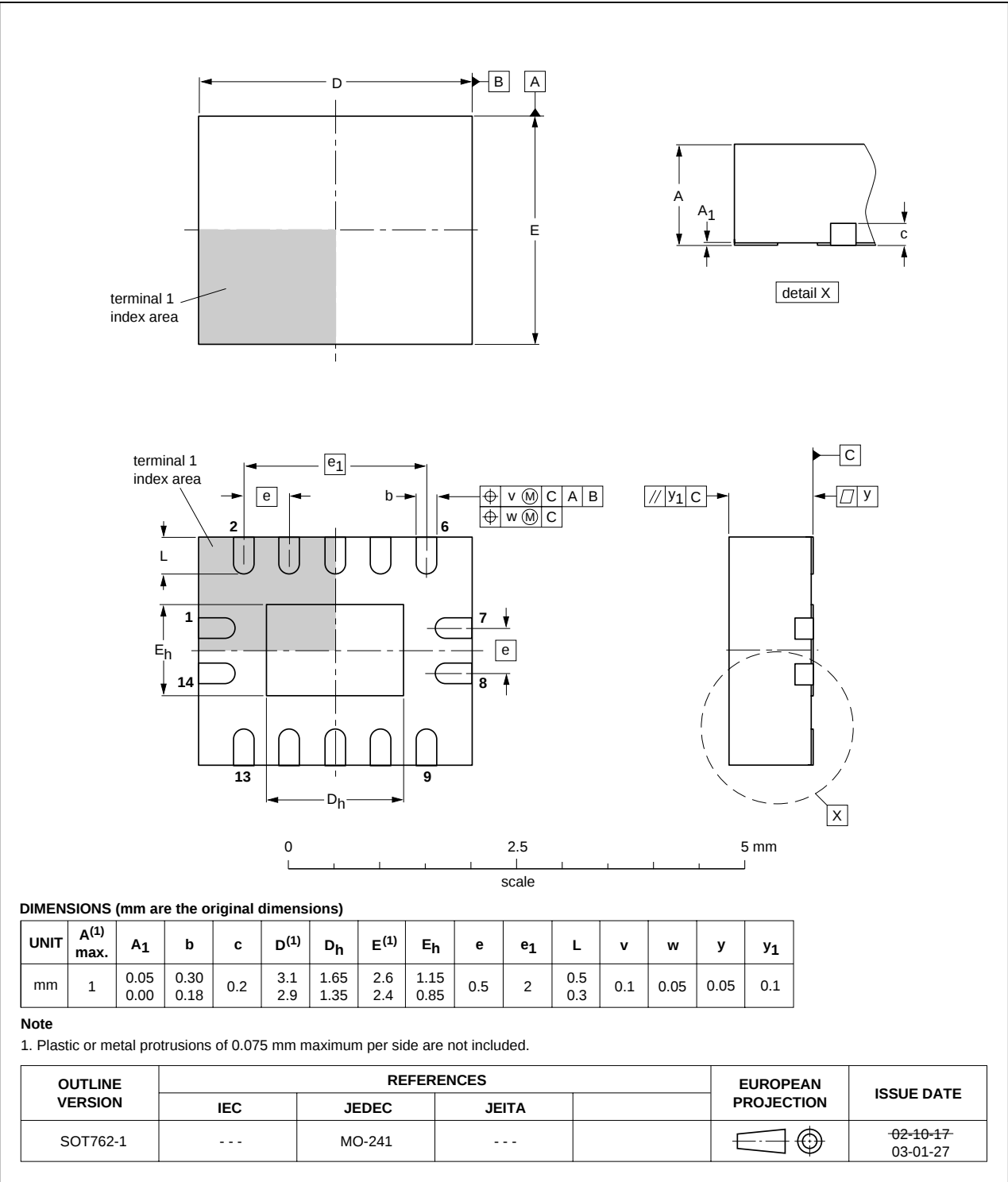


Fig 11. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT126_4	20090812	Product data sheet	-	74AHC_AHCT126_3
Modifications:	• Added type numbers 74AHC126BQ and 74AHCT126BQ (DHVQFN14 package)			
74AHC_AHCT126_3	20080425	Product data sheet	-	74AHC_AHCT126_2
74AHC_AHCT126_2	19990929	Product specification	-	74AHC_AHCT126_N_1
74AHC_AHCT126_N_1	19990112	Preliminary specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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